

### BCD-to-Decimal Decoder

The TC74HC4028A is a high speed CMOS BCD-TO-DECIMAL DECODER fabricated with silicon gate C<sup>2</sup>MOS technology.

It achieves the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation.

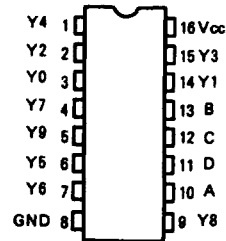
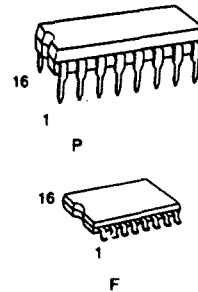
A BCD code applied to the four inputs (A ~ D) sets a high level at one of ten decoded outputs. A illegal BCD code such as eleven through fifteen sets all outputs low. This device can be used as 3-to-8 LINE DECODER when input D is held high.

This device is useful for code conversion, address decoding, memory selection, multiplexing or readout decoding.

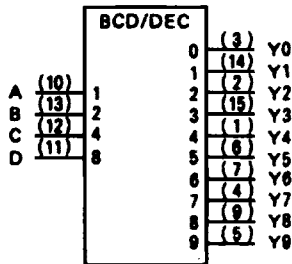
All inputs are equipped with protection circuits against static discharge or transient excess voltage.

### Features

- High Speed:  $t_{pd} = 18\text{ns(Typ.)}$  at  $V_{CC} = 5\text{V}$
- Low Power Dissipation:  $I_{CC} = 1\mu\text{A(Max.)}$  at  $T_a = 25^\circ\text{C}$
- High Noise Immunity:  $V_{NIH} = V_{NIL} = 28\% V_{CC}(\text{Min.})$
- Output Drive Capability: 10 LSTTL Loads
- Symmetrical Output Impedance:  $|I_{OH}| = I_{OL} = 4\text{mA}(\text{Min.})$
- Balanced Propagation Delays:  $t_{PLH} = t_{PHL}$
- Wide Operating Voltage Range:  $V_{CC}(\text{opr}) = 2\text{V} \sim 6\text{V}$
- Pin and Function Compatible with 4028B



Pin Assignment

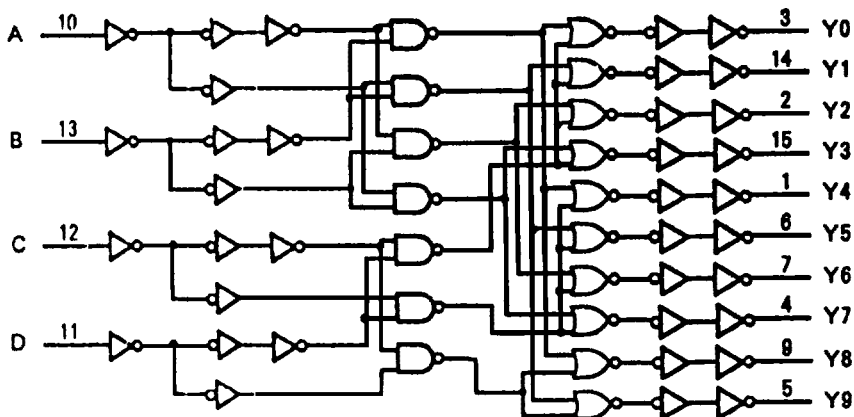


IEC Logic Symbol

Truth Table

Inputs				Outputs									Selected Output	
D	C	B	A	Y0	Y1	Y2	Y3	Y4	Y5	Y6	Y7	Y8		Y9
L	L	L	L	H	L	L	L	L	L	L	L	L	L	Y0
L	L	L	H	L	H	L	L	L	L	L	L	L	L	Y1
L	L	H	L	L	L	H	L	L	L	L	L	L	L	Y2
L	L	H	H	L	L	L	H	L	L	L	L	L	L	Y3
L	H	L	L	L	L	L	L	H	L	L	L	L	L	Y4
L	H	L	H	L	L	L	L	L	H	L	L	L	L	Y5
L	H	H	L	L	L	L	L	L	L	H	L	L	L	Y6
L	H	H	H	L	L	L	L	L	L	L	H	L	L	Y7
H	L	L	L	L	L	L	L	L	L	L	L	H	L	Y8
H	L	L	H	L	L	L	L	L	L	L	L	L	H	Y9
H	X	H	X	L	L	L	L	L	L	L	L	L	L	Note
H	H	X	X	L	L	L	L	L	L	L	L	L	L	Note

X: Don't care



Logic Diagram

## Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Supply Voltage Range	$V_{CC}$	-0.5 - 7	V
DC Input Voltage	$V_{IN}$	-0.5 - $V_{CC} + 0.5$	V
DC Output Voltage	$V_{OUT}$	-0.5 - $V_{CC} + 0.5$	V
Input Diode Current	$I_{IK}$	$\pm 20$	mA
Output Diode Current	$I_{OK}$	$\pm 20$	mA
DC Output Current	$I_{OUT}$	$\pm 25$	mA
DC $V_{CC}$ /Ground Current	$I_{CC}$	$\pm 50$	mA
Power Dissipation	$P_D$	500(DIP)*180(SOIC)	mW
Storage Temperature	$T_{stg}$	-65 - 150	°C
Lead Temperature 10sec	$T_L$	300	°C

\*500mW in the range of  $T_a = -40^\circ\text{C} \sim 65^\circ\text{C}$ . From  $T_a = 65^\circ\text{C}$  to  $85^\circ\text{C}$  a derating factor of  $-10\text{mW}/^\circ\text{C}$  shall be applied until 300mW.

## Recommended Operating Conditions

Parameter	Symbol	Value	Unit
Supply Voltage	$V_{CC}$	2 - 6	V
Input Voltage	$V_{IN}$	0 - $V_{CC}$	V
Output Voltage	$V_{OUT}$	0 - $V_{CC}$	V
Operating Temperature	$T_{opr}$	-40 - 85	°C
Input Rise and Fall Time	$t_r, t_f$	0 - 1000( $V_{CC} = 2.0\text{V}$ ) 0 - 500( $V_{CC} = 4.5\text{V}$ ) 0 - 400( $V_{CC} = 6.0\text{V}$ )	ns

## DC Electrical Characteristics

Parameter	Symbol	Test Condition	$T_a = 25^\circ\text{C}$			$T_a = -40 \sim 85^\circ\text{C}$		Unit		
			$V_{CC}$	Min	Typ.	Max.	Min.		Max.	
High-Level Input Voltage	$V_{IH}$	--	2.0	1.5	--	--	1.5	--	V	
			4.5	3.15	--	--	3.15	--		
			6.0	4.2	--	--	4.2	--		
Low-Level Input Voltage	$V_{IL}$	-	2.0	--	--	0.5	--	0.5	V	
			4.5	--	--	1.35	--	1.35		
			6.0	--	--	1.8	--	1.8		
High-Level Output Voltage	$V_{OH}$	$V_{IN} = V_{IH}$ or $V_{IL}$	$I_{OH} = -20\mu\text{A}$	2.0	1.9	2.0	--	1.9	--	V
				4.5	4.4	4.5	--	4.4	--	
				6.0	5.9	6.0	--	5.9	--	
Low-Level Output Voltage	$V_{OL}$	$V_{IN} = V_{IH}$ or $V_{IL}$	$I_{OL} = 20\mu\text{A}$	2.0	--	0.0	0.1	--	0.1	V
				4.5	--	0.0	0.1	--	0.1	
				6.0	--	0.0	0.1	--	0.1	
Input Leakage Current	$I_{IN}$	$V_{IN} = V_{CC}$ or GND	$I_{OH} = -4\text{mA}$ $I_{OH} = -5.2\text{mA}$	4.5	4.18	4.31	--	4.13	--	$\mu\text{A}$
				6.0	5.68	5.80	--	5.63	--	
				6.0	--	0.17	0.26	--	0.33	
Quiescent Supply Current	$I_{CC}$	$V_{IN} = V_{CC}$ or GND	$I_{OL} = 4\text{mA}$ $I_{OL} = 5.2\text{mA}$	4.5	--	0.18	0.26	--	0.33	$\mu\text{A}$
				6.0	--	--	4.0	--	40.0	
				6.0	--	--	4.0	--	40.0	

AC Electrical Characteristics ( $C_L = 15\text{pF}$ ,  $V_{CC} = 5\text{V}$ ,  $T_a = 25^\circ\text{C}$ , Input  $t_r = t_f = 6\text{ns}$ )

Parameter	Symbol	Test Conditon	Min.	Typ.	Max.	Unit
Output Transition Time	$t_{TLH}$ $t_{THL}$	-	-	4	8	ns
Propagation Delay Time	$t_{PLH}$ $t_{PHL}$	-	-	18	34	

AC Electrical Characteristics ( $C_L = 50\text{pF}$ , Input  $t_r = t_f = 6\text{ns}$ )

Parameter	Symbol	Test Condition	$T_a = 25^\circ\text{C}$			$T_a = -40 \sim 85^\circ\text{C}$		Unit	
			$V_{CC}$	Min.	Typ.	Max.	Min.		Max.
Output Transition Time	$t_{TLH}$ $t_{THL}$	-	2.0	-	30	75	-	95	ns
			4.5	-	8	15	-	19	
			6.0	-	7	13	-	16	
Propagation Delay Time (A, B, C, D-Y)	$t_{PLH}$ $t_{PHL}$	-	2.0	-	80	180	-	225	
			4.5	-	22	36	-	45	
			6.0	-	18	31	-	38	
Input Capacitance	$C_{IN}$	-	-	5	10	-	10	pF	
Power Dissipation Capacitance	$C_{PD(1)}$	-	-	44	-	-	-		

Note (1)  $C_{PD}$  is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation:

$$I_{CC(opp)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$$